

b) Amendments to the Claims:

Please amend claims 81 and 93. A listing of the status of all the claims that are or were in the application is provided.

--Claims 1 - 80 (Cancelled).

81. (Currently Amended): A surface optical apparatus comprising:  
a surface light emitting device;  
a substrate for supporting the surface light emitting device;  
wherein the surface light emitting device includes (i) a protrusion  
with an opening placed on a light emitting region of and (ii) ~~a light source for supplying~~  
~~light to the protrusion of~~ said surface light emitting device; and  
a photodetector to detect output light from the surface light emitting  
device.

82. (Previously Presented) A surface optical apparatus according to  
claim 81, wherein evanescent light leaks from the opening.

83. (Previously Presented) A surface optical apparatus according to  
claim 81, wherein the size of the opening is less than 100 nm.

84. (Previously Presented) A surface optical apparatus according to claim 81, wherein the shape of the protrusion is a quadrangle pyramid.

85. (Previously Presented) A surface optical apparatus according to claim 81, wherein said surface light emitting device is supported by said substrate through an elastic supporter.

Claims 86 - 88 (Cancelled).

89. (Previously Presented) A surface optical apparatus according to claim 81, wherein said surface light emitting device comprises a surface emitting semiconductor laser.

90. (Previously Presented) A surface optical apparatus according to claim 81, wherein said surface light emitting device comprises thin semiconductor layers grown on another substrate, and said another substrate is mounted on said substrate.

91. (Previously Presented) A surface optical apparatus according to claim 89, wherein the surface emitting semiconductor laser includes at least one of a layer of GaAs, a layer of AlGaAs and a layer of InGaAs.

92. (Previously Presented) A surface optical apparatus according to claim 89, wherein the surface emitting semiconductor laser includes at least one of a layer of GaN, a layer of AlGaIn and a layer of InGaIn.

93. (Currently Amended): A surface optical apparatus comprising:  
a supporter;  
a surface light emitting device on the supporter; and  
a photodetector to detect output light from the surface light emitting device, wherein the surface light emitting device ~~has (i) includes a protrusion with an~~  
opening placed on a light emitting region of said surface light emitting device ~~portion for~~  
~~emitting light and (ii) a light source for supplying light to the opening portion.~~

94. (Previously Presented) A surface optical apparatus according to claim 93, wherein said supporter is shaped into a cantilever.

95. (Previously Presented) A surface optical apparatus according to claim 93, wherein said supporter is shaped as a trapezoidal cantilever whose central portion is removed.

96. (Previously Presented) A surface optical apparatus according to claim 93, wherein said surface light emitting device comprises a surface emitting semiconductor laser.

97. (Cancelled).

98. (Previously Presented) A surface optical apparatus according to claim 96, wherein the surface emitting semiconductor laser includes at least one of a layer of GaAs, a layer of AlGaAs and a layer of InGaAs.

99. (Previously Presented) A surface optical apparatus according to claim 96, wherein the surface emitting semiconductor laser includes at least one of a layer of GaN, a layer of AlGaN and a layer of InGaN.--